

DualCool™ N-Ch NexFET™ Power MOSFET

FEATURES

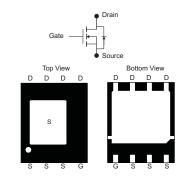
- Ultra Low Q_q and Q_{qd}
- DualCool™ Package
- **Optimized for 2-Sided Cooling**
- **Low Thermal Resistance**
- **Avalanche Rated**
- **Pb Free Terminal Plating**
- **RoHS Compliant**
- **Halogen Free**
- SON 5-mm x 6-mm Plastic Package

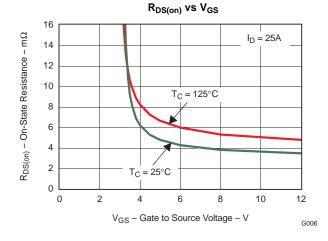
APPLICATIONS

- Point-of-Load Synchronous Buck in **Networking, Telecom and Computing Systems**
- **Optimized for Control FET Applications**

DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in power conversion applications.





PRODUCT SUMMARY

V_{DS}	Drain to Source Voltage	25	V	
Q_g	Gate Charge Total (4.5V) 6.7			nC
Q_{gd}	Gate Charge Gate to Drain 1.9		nC	
D	Drain to Source On Resistance	$V_{GS} = 4.5V$	5.4	mΩ
R _{DS(on)}	Diam to Source On Resistance	$V_{GS} = 10V$	3.6	mΩ
$V_{GS(th)}$	Threshold Voltage 1.8			V

ORDERING INFORMATION

Device	Package	Media	Qty	Ship	
CSD16408Q5C	SON 5-mm × 6-mm Plastic Package	13-Inch Reel	2500	Tape and Reel	

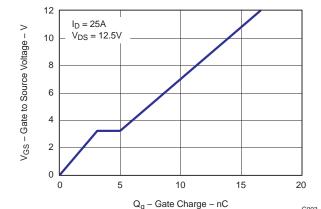
ABSOLUTE MAXIMUM RATINGS

T _A = 2	5°C unless otherwise stated	VALUE	UNIT
V_{DS}	Drain to Source Voltage	25	V
V_{GS}	Gate to Source Voltage	+16 / -12	٧
1	Continuous Drain Current, T _C = 25°C	113	Α
I _D	Continuous Drain Current (1)	22	Α
I_{DM}	Pulsed Drain Current, T _A = 25°C (2)	141	Α
P_D	Power Dissipation (1)	3.1	W
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	ů
E _{AS}	Avalanche Energy, single pulse $I_D = 23A, L = 0.1 mH, R_G = 25\Omega$	126	mJ

(1) Typical $R_{\theta,JA} = 41^{\circ}\text{C/W}$ on a 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 0.06-inch (1.52-mm) thick FR4

GATE CHARGE

(2) Pulse duration ≤300µs, duty cycle ≤2%



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

25°C unless otherwise stated

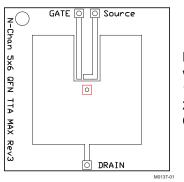
$T_A = 25^\circ$	C unless otherwise stated				
	PARAMETER	TEST CONDITIONS	MIN T	YP MAX	UNIT
Static C	haracteristics				
BV_{DSS}	Drain to Source Voltage	$V_{GS} = 0V, I_D = 250\mu A$	25		V
I _{DSS}	Drain to Source Leakage	$V_{GS} = 0V, V_{DS} = 20V$		1	μΑ
I _{GSS}	Gate to Source Leakage	$V_{DS} = 0V, V_{GS} = +16/-12V$		100	nA
$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.4	1.8 2.1	V
D	Drain to Source On Resistance	$V_{GS} = 4.5V, I_D = 25A$		5.4 6.8	mΩ
R _{DS(on)}	Drain to Source On Resistance	$V_{GS} = 10V, I_D = 25A$;	3.6 4.5	mΩ
9 _{fs}	Transconductance	$V_{DS} = 15V, I_D = 25A$		60	S
Dynami	Characteristics				
C _{ISS}	Input Capacitance		9	90 1300	pF
Coss	Output Capacitance	$V_{GS} = 0V, V_{DS} = 12.5V, f = 1MHz$	7	60 1000	pF
C _{RSS}	Reverse Transfer Capacitance			75 100	pF
R_g	Series Gate Resistance			0.8 1.6	Ω
Qg	Gate Charge Total (4.5V)			6.7 8.9	nC
Q _{gd}	Gate Charge – Gate to Drain	V _{DS} = 12.5V, I _D = 25A		1.9	nC
Q_{gs}	Gate Charge – Gate to Source	V _{DS} = 12.5V, I _D = 25A	;	3.1	nC
$Q_{g(th)}$	Gate Charge at Vth			1.8	nC
Q _{OSS}	Output Charge	V _{DS} = 13V, V _{GS} = 0V	1:	5.7	nC
t _{d(on)}	Turn On Delay Time		1	1.3	ns
t _r	Rise Time	$V_{DS} = 12.5V, V_{GS} = 4.5V,$		25	ns
t _{d(off)}	Turn Off Delay Time	$I_D = 25A$, $R_G = 2\Omega$		11	ns
t _f	Fall Time		10	0.8	ns
Diode C	haracteristics				
V _{SD}	Diode Forward Voltage	$I_{S} = 25A, V_{GS} = 0V$		0.8 1	V
Q_{rr}	Reverse Recovery Charge	$V_{DD} = 13V$, $I_F = 25A$, $di/dt = 300A/\mu s$		17	nC
t _{rr}	Reverse Recovery Time	$V_{DD} = 13V$, $I_F = 25A$, $di/dt = 300A/\mu s$		21	ns

THERMAL CHARACTERISTICS

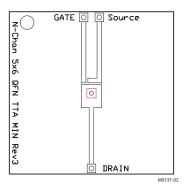
	PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal Resistance Junction to Case (Top Source) ⁽¹⁾			3.1	°C/W
$R_{\theta JC}$	Thermal Resistance Junction to Case (Bottom Drain) ⁽¹⁾			1.9	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient ⁽¹⁾ (2)			51	°C/W

 $R_{\theta JC}$ is determined with the device mounted on a 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu pad on a 1.5-inch × 1.5-inch (3.81-cm × 3.81-cm), 0.06-inch (1.52-mm) thick FR4 PCB. $R_{\theta JC}$ is specified by design, whereas $R_{\theta JA}$ is determined by the user's board design. Device mounted on FR4 material with 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu.





Max $R_{\theta JA} = 51^{o}C/W$ when mounted on 1 inch² (6.45 cm²) of 2-oz. (0.071-mm thick) Cu.



Max $R_{\theta JA} = 125^{o} C/W$ when mounted on minimum pad area of 2-oz. (0.071-mm thick) Cu.

TYPICAL MOSFET CHARACTERISTICS

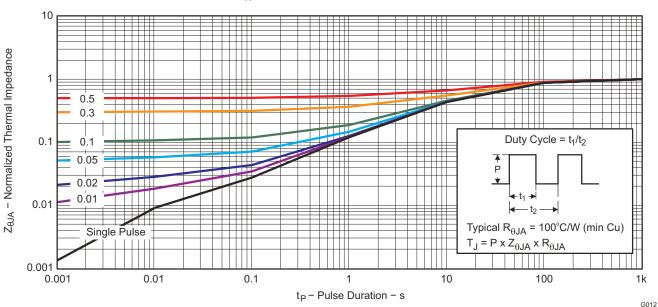


Figure 1. Transient Thermal Impedance



TYPICAL MOSFET CHARACTERISTICS (continued)

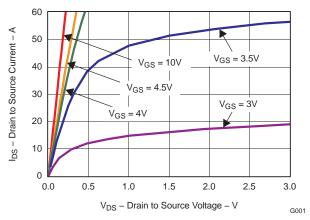


Figure 2. Saturation Characteristics

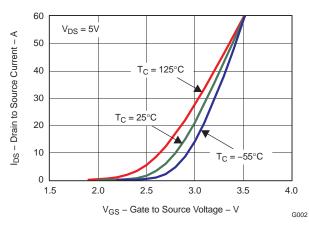


Figure 3. Transfer Characteristics

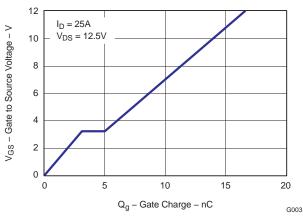


Figure 4. Gate Charge

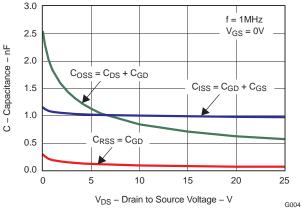


Figure 5. Capacitance

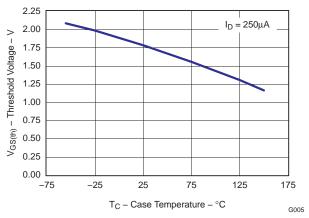


Figure 6. Threshold Voltage vs. Temperature

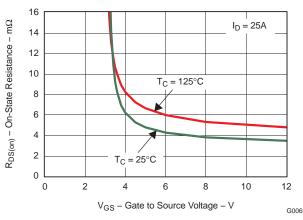


Figure 7. On-State Resistance vs. Gate to Source Voltage



TYPICAL MOSFET CHARACTERISTICS (continued)

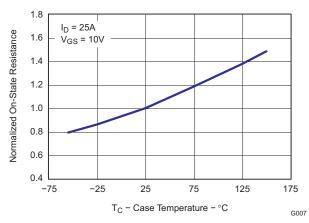


Figure 8. Normalized On-State Resistance vs. Temperature

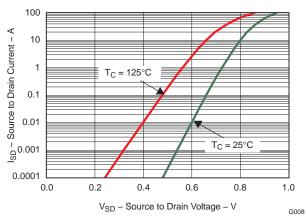


Figure 9. Typical Diode Forward Voltage

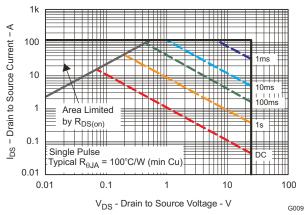


Figure 10. Maximum Safe Operating Area

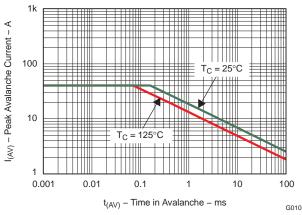


Figure 11. Single Pulse Unclamped Inductive Switching

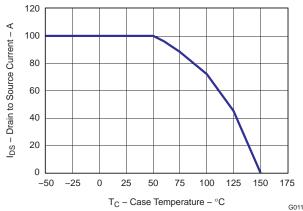
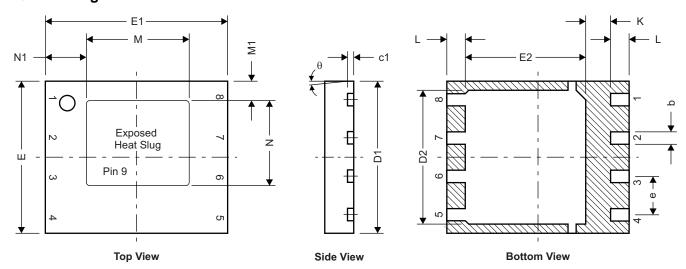


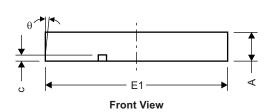
Figure 12. Maximum Drain Current vs. Temperature



MECHANICAL DATA

Q5C Package Dimensions





DualCool™Pinout				
Pin#	Label			
1, 2, 3, 9	Source			
4	Gate			
5, 6, 7, 8	Drain			

M0162-01

DIM	MILLIM	ETERS	INCHES		
DIN	MIN	MAX	MIN	MAX	
Α	0.950	1.050	0.037	0.039	
b	0.360	0.460	0.014	0.018	
С	0.150	0.250	0.006	0.010	
c1	0.150	0.250	0.006	0.010	
D1	4.900	5.100	0.193	0.201	
D2	4.320	4.520	0.170	0.178	
Е	4.900	5.100	0.193	0.201	
E1	5.900	6.100	0.232	0.240	
E2	3.920	4.12	0.154	0.162	
е	1.27	TYP	0.050		
К	0.760	_	0.030	_	
L	0.510	0.710	0.020	0.028	
θ	_	-	-	_	
M	3.260	3.460	0.128	0.136	
M1	0.520	0.720	0.020	0.028	
N	2.720	2.920	0.107	0.115	
N1	1.227	1.427	0.048	0.056	

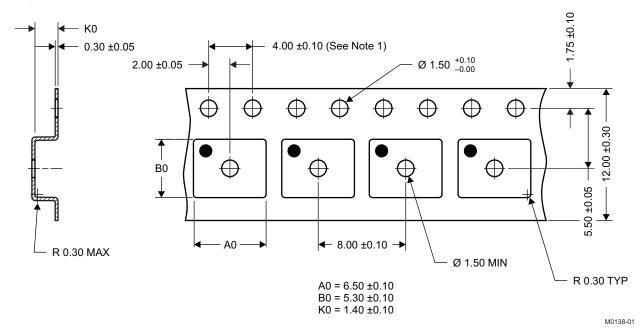


Recommended PCB Pattern F6 F1 F7 F7 F1 F7 F1 F7 FM139,01

DIM	MILLIN	IETERS	INCHES		
DIW	MIN	MAX	MIN	MAX	
F1	6.205	6.305	0.244	0.248	
F2	4.46	4.56	0.176	0.18	
F3	4.46	4.56	0.176	0.18	
F4	0.65	0.7	0.026	0.028	
F5	0.62	0.67	0.024	0.026	
F6	0.63	0.68	0.025	0.027	
F7	0.7	0.8	0.028	0.031	
F8	0.65	0.7	0.026	0.028	
F9	0.62	0.67	0.024	0.026	
F10	4.9	5	0.193	0.197	
F11	4.46	4.56	0.176	0.18	

For recommended circuit layout for PCB designs, see application note *Reducing Ringing Through PCB Layout Techniques* (SLPA005).

Q5 Tape and Reel Information



Notes:

- 1. 10-sprocket hole-pitch cumulative tolerance ±0.2
- 2. Camber not to exceed 1mm in 100mm, noncumulative over 250mm
- 3. Material: black static-dissipative polystyrene
- 4. All dimensions are in mm, unless otherwise specified.
- 5. A0 and B0 measured on a plane 0.3mm above the bottom of the pocket
- 6. MSL1 260°C (IR and convection) PbF reflow compatible

SLPS263B - DECEMBER 2009-REVISED SEPTEMBER 2010



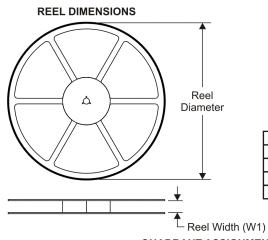
REVISION HISTORY

Changes from Original (December 2009) to Revision A		
Changed the labels on the Bottom View pinout image	1	
Changes from Revision A (February) to Revision B	Page	
the Package Marking Information section	7	

PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

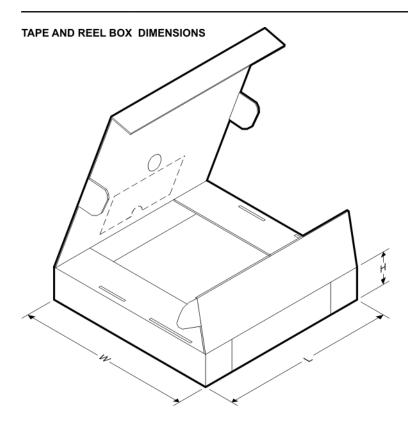
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD16408Q5C	SON	DQU	8	2500	330.0	12.8	6.5	5.3	1.4	8.0	12.0	Q1

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*All dimensions are nominal

	Device	Device Package Type		Package Drawing Pins		Length (mm)	Width (mm)	Height (mm)	
I	CSD16408Q5C	SON	DQU	8	2500	335.0	335.0	32.0	

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